

# 2SP0115T2Ax-FF150R12ME3G Preliminary Data Sheet

Compact, high-performance, plug-and-play dual-channel IGBT driver based on SCALE-2 technology for individual and parallel-connected modules

#### **Abstract**

The SCALE-2 plug-and-play driver 2SP0115T2Ax-FF150R12ME3G is a compact dual-channel intelligent gate driver designed for Infineon's EconoDUAL $^{\text{TM}}$  IGBTs FF150R12ME3G. The driver features an electrical interface with a built-in DC/DC power supply.

For drivers adapted to other types of high-power and high-voltage IGBT modules, refer to

www.IGBT-Driver.com/go/plug-and-play

#### **Features**

- ✓ Plug-and-play solution
- ✓ Allows parallel connection of IGBT modules
- ✓ Shortens application development time
- ✓ Extremely reliable; long service life
- ✓ Built-in DC/DC power supply
- ✓ 20-pin flat cable interface
- ✓ Duty cycle 0... 100%
- ✓ Active clamping of V<sub>ce</sub> at turn-off
- ✓ IGBT short-circuit protection
- ✓ Monitoring of supply voltage
- ✓ Safe isolation to EN 50178
- ✓ UL compliant
- ✓ Suitable for FF150R12ME3G

## **Applications**

- ✓ Wind-power converters
- ✓ Industrial drives
- **✓** UPS
- ✓ Power-factor correctors
- ✓ Traction
- ✓ Railroad power supplies
- ✓ Welding
- ✓ SMPS
- ✓ Radiology and laser technology
- ✓ Research
- and many others

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## **Safety Notice!**

The data contained in this data sheet is intended exclusively for technically trained staff. Handling all high-voltage equipment involves risk to life. Strict compliance with the respective safety regulations is mandatory!

Any handling of electronic devices is subject to the general specifications for protecting electrostatic-sensitive devices according to international standard IEC 60747-1, Chapter IX or European standard EN 100015 (i.e. the workplace, tools, etc. must comply with these standards). Otherwise, this product may be damaged.

## **Important Product Documentation**

This data sheet contains only product-specific data. For a detailed description, must-read application notes and common data that apply to the whole series, please refer to "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers" on www.IGBT-Driver.com/go/2SP0115T.

When applying SCALE-2 plug-and-play drivers, please note that these drivers are specifically adapted to a particular type of IGBT module. Therefore, the type designation of SCALE-2 plug-and-play drivers also includes the type designation of the corresponding IGBT module. These drivers are not valid for IGBT modules other than those specified. Incorrect use may result in failure.

#### **Mechanical Dimensions**

Dimensions: See "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers" Mounting principle: Soldered onto EconoDUAL<sup>™</sup> module FF150R12ME3G

## **Absolute Maximum Ratings**

Parameter	Remarks	Min	Max	Unit
Supply voltage V <sub>CC</sub>	VCC to GND	0	16	V
Logic input and output voltages	To GND	-0.5	VCC+0.	5 V
SO <sub>x</sub> current	Fault condition, total current		20	mA
Gate peak current I <sub>out</sub>	Note 1	-8	+15	Α
Average supply current I <sub>CC</sub>	Note 2		290	mA
Output power per gate	Ambient temperature <70°C (Note 3)		1.2	W
	Ambient temperature 85°C (Note 3)		1	W
Switching frequency F			40	kHz
Test voltage (50Hz/1min.)	Primary to secondary (Note 17)		3800	$V_{AC(eff)}$
	Secondary to secondary (Note 17)		3800	$V_{AC(eff)}$
DC-link voltage	Note 4		800	v
dV/dt	Rate of change of input to output voltage (Note 5)		50	kV/μs
Operating voltage	Primary/secondary, secondary/secondary		1200	$V_{peak}$
Operating temperature	Note 20	-20	+85	°C
Storage temperature		-40	+90	°C



## **Recommended Operating Conditions**

Parameter	Remarks	Min	Тур	Max	Unit
Supply voltage $V_{CC}$ Resistance from TB to GND $SO_x$ current	To GND Blocking time≠0, ext. value Fault condition, 3.3V logic	14.5 128	15	15.5 ∞ 4	V kΩ mA

## **Electrical Characteristics**

Power Supply	Remarks	Min	Тур	Max	Unit
Supply current I <sub>CC</sub>	Without load		33		mA
Efficiency η	Internal DC/DC converter		85		%
Coupling capacitance C <sub>io</sub>	Primary side to secondary side, total, per	channel	23		pF
Power Supply Monitoring	Remarks	Min	Тур	Max	Unit
Supply threshold V <sub>CC</sub>	Primary side, clear fault	11.9	12.6	13.3	V
	Primary side, set fault (Note 6)	11.3	12.0	12.7	V
Monitoring hysteresis	Primary side, set/clear fault	0.35			V
Supply threshold V <sub>isox</sub> -V <sub>eex</sub>	Secondary side, clear fault	12.1	12.6	13.1	V
	Secondary side, set fault (Note 7)	11.5	12.0	12.5	V
Monitoring hysteresis	Secondary side, set/clear fault	0.35			V
Supply threshold V <sub>eex</sub> -V <sub>COMx</sub>	Secondary side, clear fault	5	5.15	5.3	V
	Secondary side, set fault (Note 7)	4.7	4.85	5	V
Monitoring hysteresis	Secondary side, set/clear fault	0.15			V
Logic Inputs and Outputs	Remarks	Min	Тур	Max	Unit
Input impedance	V(INx) > 3V (Note 8)	3.5	4.1	4.6	kΩ
Turn-on threshold	V(INx) (Note 9)		2.6		V
Turn-off threshold	V(INx) (Note 9)		1.3		V
SOx output voltage	Fault condition, I(SOx)<8mA			0.7	V
Short-circuit Protection	Remarks	Min	Тур	Max	Unit
Vce-monitoring threshold	Between auxiliary terminals		10.2		V
Response time	DC-link voltage > 550V (Note 10)		5.4		μs
Delay to IGBT turn-off	After the response time (Note 11)		1.4		μs
Blocking time	After fault (Note 12)		90		ms

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$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Timing Characteristics	Remarks	Min	Тур	Max	Unit
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	Turn-on delay t <sub>d(on)</sub>	Note 13		75		ns
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	Turn-off delay t <sub>d(off)</sub>	Note 13		65		ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Jitter of turn-on delay	Note 19		±2		ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Jitter of turn-off delay	Note 19		±4		ns
Dead time between outputs Jitter of dead timeHalf-bridge mode3 ±50μsTransmission delay of fault stateNote 15400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor Rg(on) Turn-off gate resistor Rg(off)Note 168.2ΩGate voltage at turn-on Gate-voltage at turn-off P = 1.2W9.2VFeate resistance to COMx4.7VElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 17) Secondary to secondary side (Note 17) Secondary to secondary side (Note 18) Secondary to secondary side (Note 18)12.6 Secondary to secondary side (Note 18) Secondary to secondary side (Note 18)12.6 Secondary to secondary side (Note 18) Secondary to secondary side (Note 18)12.3 Secondary to secondary side (Note 18) Secondary	Output rise time $t_{r(out)}$	$G_x$ to $E_x$ (Note 14)		5		ns
Jitter of dead timeHalf-bridge mode $\pm 50$ nsTransmission delay of fault stateNote 15400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{g(on)}$ Note 168.2 $\Omega$ Turn-off gate resistor $R_{g(off)}$ Note 168.2 $\Omega$ Gate voltage at turn-on15 $V$ Gate-voltage at turn-off $P = 0W$ $-9.2$ $V$ $P = 1.2W$ $-7.1$ $V$ Gate resistance to COMx $4.7$ $K\Omega$ Electrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 17)380038503900 $V_{eff}$ Partial discharge extinction volt.Primary to secondary side (Note 18)1220 $V_{peak}$ Creepage distancePrimary to secondary side (Note 18)1200 $V_{peak}$ Creepage distancePrimary to secondary side12.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3mmClearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mm	Output fall time $t_{f(out)}$	$G_x$ to $E_x$ (Note 14)		10		ns
Transmission delay of fault state Note 15 $400$ ns $\frac{1}{1}$ Note 16 $\frac{1}{1}$ Note 17 $\frac{1}{1}$ Note 18 $\frac{1}{1}$ Note 19 $\frac{1}{1}$ Note	Dead time between outputs	Half-bridge mode		3		μs
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Jitter of dead time	Half-bridge mode		±50		ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Transmission delay of fault state	Note 15		400		ns
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	Outputs	Remarks	Min	Тур	Max	Unit
Gate voltage at turn-on $P = 0W$ $P = 0W$ $P = 1.2W$	Turn-on gate resistor R <sub>g(on)</sub>	Note 16		8.2		Ω
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-off gate resistor R <sub>g(off)</sub>	Note 16		8.2		Ω
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate voltage at turn-on			15		V
	Gate-voltage at turn-off	P = 0W		-9.2		V
Electrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 17) Secondary to secondary side (Note 17)3800 38503900 3850VeffPartial discharge extinction volt.Primary to secondary side (Note 18) Secondary to secondary side (Note 18)1220 1200 VpeakVpeak VpeakCreepage distancePrimary to secondary side Secondary to secondary side Primary to NTC12.6 6.6 6.5mmClearance distancePrimary to secondary side Primary to secondary side Secondary to secondary side12.3 6.6mm		P = 1.2W		-7.1		V
Test voltage (50Hz/1s)  Primary to secondary side (Note 17)  Secondary to secondary side (Note 17)  Partial discharge extinction volt.  Primary to secondary side (Note 18)  Secondary to secondary side (Note 18)  Primary to secondary side (Note 18)  Primary to secondary side  Primary to secondary side  Secondary to secondary side  Primary to secondary side  Secondary to secondary side  Primary to NTC  Clearance distance  Primary to secondary side  Primary to secondary side  Secondary to secondary side  Secondary to secondary side  Primary to secondary side  Secondary to secondary side  Secondary to secondary side	Gate resistance to COMx			4.7		kΩ
Secondary to secondary side (Note 17) 3800 3850 3900 V <sub>eff</sub> Partial discharge extinction volt. Primary to secondary side (Note 18) 1220 V <sub>peak</sub> Secondary to secondary side (Note 18) 1200 V <sub>peak</sub> Creepage distance Primary to secondary side 12.6 mm  Secondary to secondary side 6.6 mm  Primary to NTC 6.5 mm  Clearance distance Primary to secondary side 12.3 mm  Secondary to secondary side 6.6 mm	Electrical Isolation	Remarks	Min	Тур	Max	Unit
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Test voltage (50Hz/1s)	Primary to secondary side (Note 17)	3800	3850	3900	$V_{\text{eff}}$
Secondary to secondary side (Note 18) 1200 V <sub>peak</sub> Creepage distance Primary to secondary side 12.6 mm  Secondary to secondary side 6.6 mm  Primary to NTC 6.5 mm  Clearance distance Primary to secondary side 12.3 mm  Secondary to secondary side 6.6 mm		Secondary to secondary side (Note 17)	3800	3850	3900	$V_{\text{eff}}$
Creepage distance Primary to secondary side 12.6 mm  Secondary to secondary side 6.6 mm  Primary to NTC 6.5 mm  Clearance distance Primary to secondary side 12.3 mm  Secondary to secondary side 6.6 mm	Partial discharge extinction volt.	Primary to secondary side (Note 18)	1220			$V_{peak}$
Secondary to secondary side 6.6 mm  Primary to NTC 6.5 mm  Clearance distance Primary to secondary side 12.3 mm  Secondary to secondary side 6.6 mm		Secondary to secondary side (Note 18)	1200			$V_{peak}$
Primary to NTC 6.5 mm  Clearance distance Primary to secondary side 12.3 mm  Secondary to secondary side 6.6 mm	Creepage distance	Primary to secondary side	12.6			
Clearance distance Primary to secondary side 12.3 mm Secondary to secondary side 6.6 mm		Secondary to secondary side	6.6			mm
Secondary to secondary side 6.6 mm		Primary to NTC	6.5			mm
·	Clearance distance	Primary to secondary side	12.3			mm
Primary to NTC 6.5 mm		Secondary to secondary side	6.6			mm
		Primary to NTC	6.5			mm

All data refer to +25°C and  $V_{CC} = 15V$  unless otherwise specified

## Footnotes to the Key Data

- 1) The gate current is limited by the gate resistors located on the driver.
- 2) If the specified value is exceeded, this indicates a driver overload. It should be noted that the driver is not protected against overload.
- 3) If the specified value is exceeded, this indicates a driver overload. It should be noted that the driver is not protected against overload. From 70°C to 85°C, the maximum permissible output power can be linearly interpolated from the given data.
- 4) This limit is due to active clamping. Refer to the "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers".
- 5) This specification guarantees that the drive information will be transferred reliably even at a high DC-link voltage and with ultra-fast switching operations.



- 6) Undervoltage monitoring of the primary-side supply voltage (VCC to GND). If the voltage drops below this limit, a fault is transmitted to the corresponding outputs and the IGBTs are switched off.
- 7) Undervoltage monitoring of the secondary-side supply voltage (Visox to Veex and Veex to COMx which correspond with the approximate turn-on and turn-off gate-emitter voltages). If the corresponding voltage drops below this limit, the IGBT is switched off and a fault is transmitted to the corresponding output.
- 8) The input impedance can be modified to values  $< 18 \text{ k}\Omega$  (customer-specific solution).
- 9) Turn-on and turn-off threshold values can be increased (customer-specific solution).
- 10) The resulting pulse width of the direct output of the gate drive unit for short-circuit type I (excluding the delay of the gate resistors) is the sum of response time plus delay to IGBT turn-off.
- 11) The turn-off event of the IGBT is delayed by the specified time after the response time.
- 12) Factory set value. The blocking time can be reduced with an external resistor. Refer to the "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers".
- 13) Measured from the transition of the turn-on or turn-off command at the driver input to direct output of the gate drive unit (excluding the delay of the gate resistors).
- 14) Output rise and fall times are measured between 10% and 90% of the nominal output swing with an output load of  $10\Omega$  and 40nF. The values are given for the driver side of the gate resistors. The time constant of the output load in conjunction with the present gate resistors leads to an additional delay at the load side of the gate resistors.
- 15) Transmission delay of the fault state from the secondary side to the primary status outputs.
- 16) The gate resistors can be leaded or surface mounted. CONCEPT reserves the right to determine which type will be used. Typically, higher quantities will be produced with SMD resistors and small quantities with leaded resistors.
- 17) HiPot testing (= dielectric testing) must generally be restricted to suitable components. This gate driver is suited for HiPot testing. Nevertheless, it is strongly recommended to limit the testing time to 1s slots as stipulated by EN 50178. Excessive HiPot testing at voltages much higher than  $850V_{AC(eff)}$  may lead to insulation degradation. No degradation has been observed over 1min. testing at  $3800V_{AC(eff)}$ . Every production sample shipped to customers has undergone 100% testing at the given value or higher ( $<5100V_{eff}$ ) for 1s.
- 18) Partial discharge measurement is performed in accordance with IEC 60270 and isolation coordination specified in EN 50178. The partial discharge extinction voltage between primary and either secondary side is coordinated for safe isolation to EN 50178.
- 19) Jitter measurements are performed with input signals INx switching between 0V and 15V referred to GND, with a corresponding rise time and fall time of 8ns.
- 20) A version with extended operating temperature range of —40°C...85°C (2SP0115T2B0) can also be supplied.

## Legal Disclaimer

This data sheet specifies devices but cannot promise to deliver any specific characteristics. No warranty or guarantee is given – either expressly or implicitly – regarding delivery, performance or suitability.

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## **Ordering Information**

The general terms and conditions of delivery of CT-Concept Technologie AG apply.

#### **CONCEPT Driver Type #**

#### **Related IGBT**

2SP0115T2A0-FF150R12ME3G (Temperature range -20°C85°C)	FF150R12ME3G
2SP0115T2B0-FF150R12ME3G (Temperature range -40°C85°C)	FF150R12ME3G

Product home page: <a href="https://www.IGBT-Driver.com/go/2SP0115T">www.IGBT-Driver.com/go/2SP0115T</a>

Refer to <a href="https://www.IGBT-Driver.com/go/nomenclature">www.IGBT-Driver.com/go/nomenclature</a> for information on driver nomenclature

### **Information about Other Products**

For other drivers, evaluation systems product documentation and application support

Please click: www.IGBT-Driver.com

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